ELECTRONICS, INC.
44 FARRAND STREET
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1I5400 thru 1N5408
Axial Lead Standard Recovery
Silicon Rectifiers, 3 Amp, DO–201AD

Features:

- 3 Amp Operation at T_A = +75°C with no Thermal Runaway
- High Current Capability
- Low Leakage

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified, Note 1)

Peak Repetitive Reverse Voltage, V_{RRM}
DC Reverse Voltage, V_R
- 1N5400 . . . . . 50V
- 1N5401 . . . . . 100V
- 1N5402 . . . . . 200V
- 1N5403 . . . . . 300V
- 1N5404 . . . . . 400V
- 1N5405 . . . . . 500V
- 1N5406 . . . . . 600V
- 1N5407 . . . . . 800V
- 1N5408 . . . . . 1000V

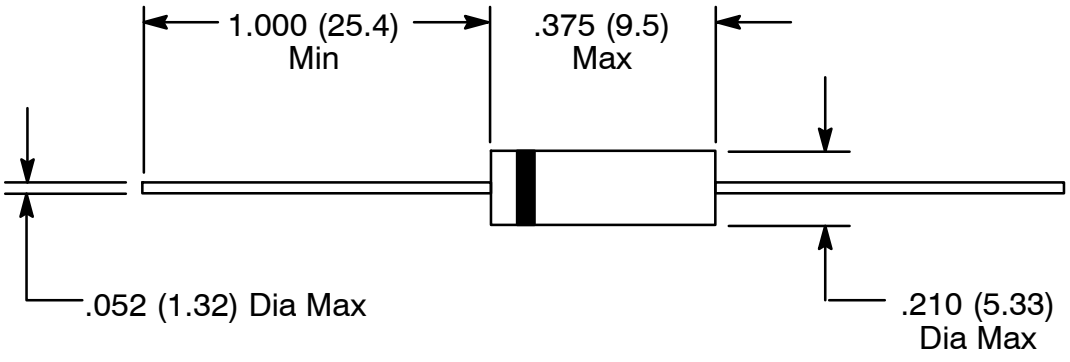
Maximum RMS Voltage
- 1N5400 . . . . . 35V
- 1N5401 . . . . . 70V
- 1N5402 . . . . . 140V
- 1N5403 . . . . . 210V
- 1N5404 . . . . . 280V
- 1N5405 . . . . . 350V
- 1N5406 . . . . . 420V
- 1N5407 . . . . . 560V
- 1N5408 . . . . . 700V

Average Rectified Current (.375” Lead Length, T_A = +75°C), I_O 3A
Peak Forward Surge Current, $I_{F(surge)}$
(Superimposed on a Rated Load, 8.3ms Single Half–Sine Wave) 200A
Total Device Dissipation, P_D 6.25W
Derate Above +25°C . . . . . 50mW/°C
Operating Junction Temperature Range, T_J . . . . . –55° to +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C
Thermal Resistance, Junction–to–Ambient, R_{thJA} . . . . . +20°C/W

Note 1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Maximum Reverse Current	I_R	Rated DC Voltage	T_A = +25°C	–	–	5.0	µA
			T_A = +100°C	–	–	500	µA
Maximum Forward Voltage	V_F	i_F = 3A		–	–	1.2	V
Average Reverse Current	$I_{R(AV)}$	Full Cycle, T_A = +105°C		–	–	0.5	mA
Junction Capacitance		V_R = 4V, f = 1MHz		–	30	–	pF



Color Band Denotes Cathode